



**GP**  
**ELECTRONICS**

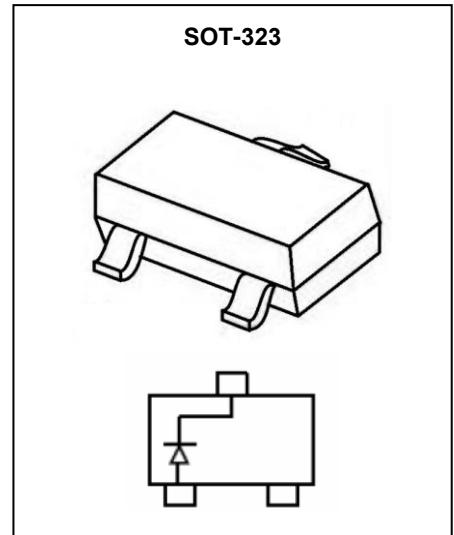
**BAS21W**  
**Switching Diode**

## BAS21W Switching Diode

### Feature

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

**MARKING: KT3**



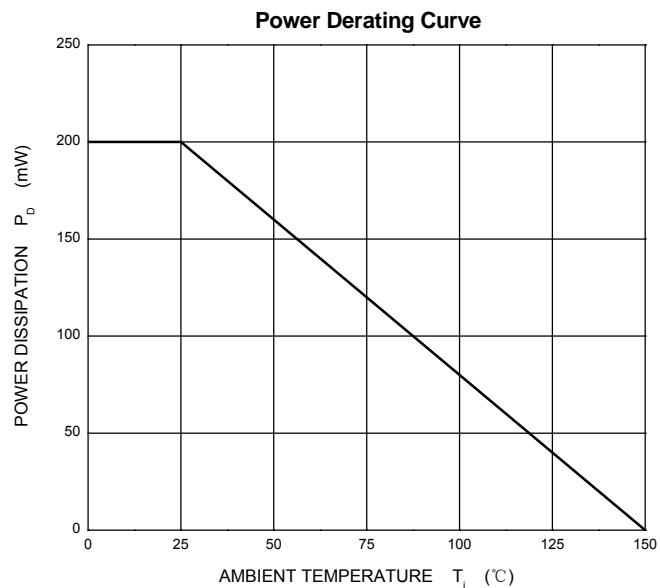
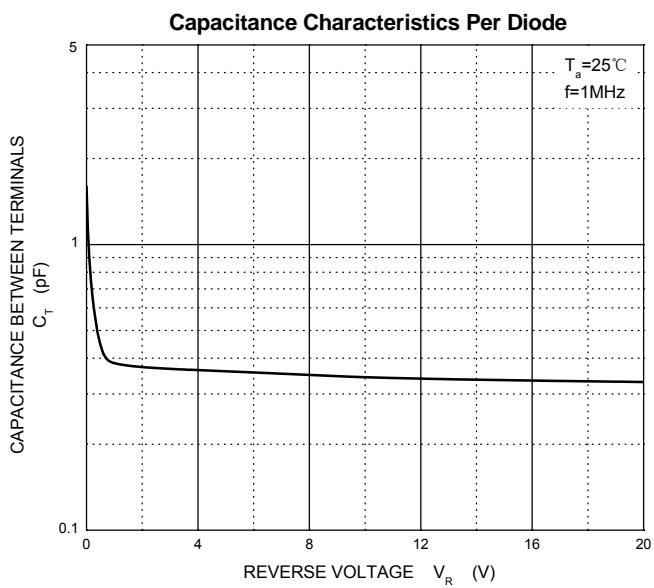
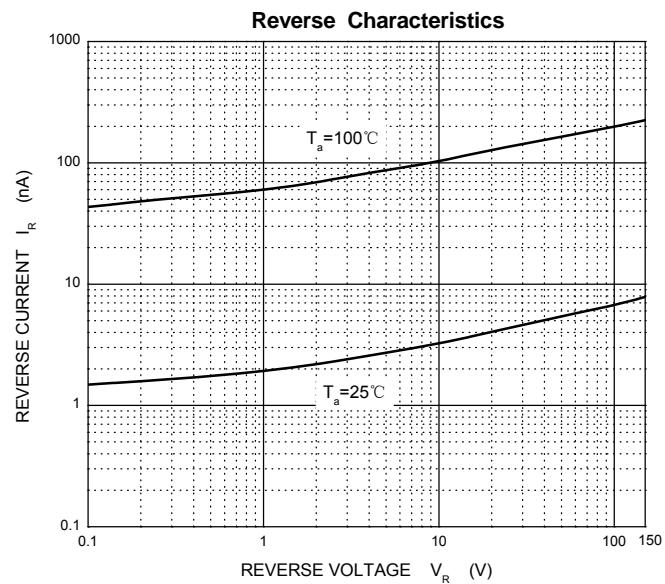
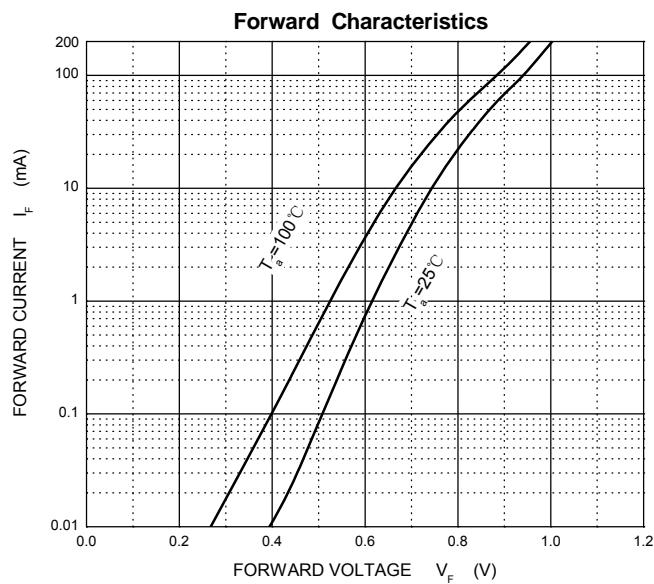
### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

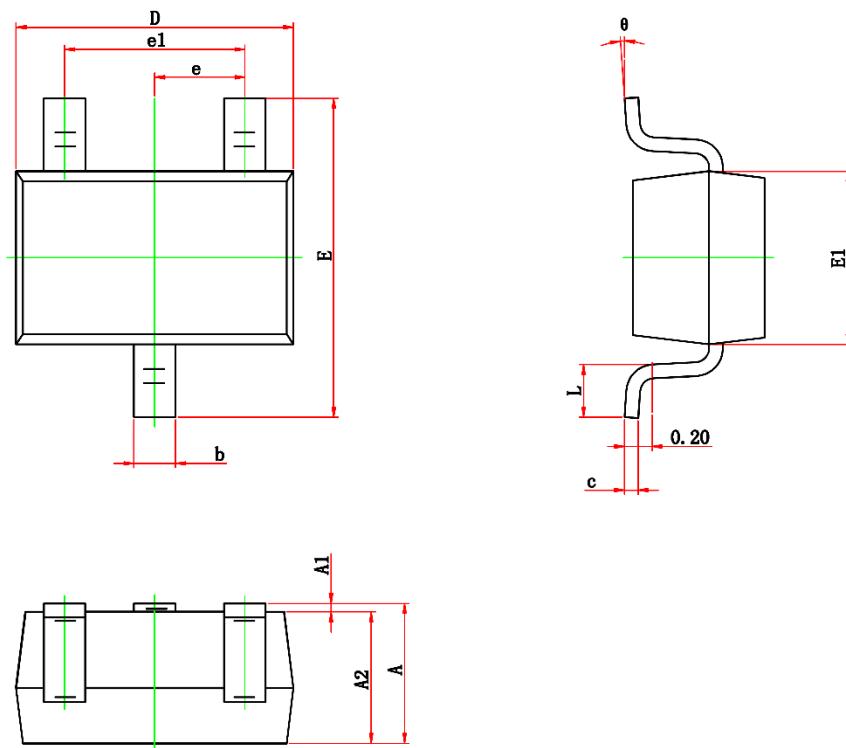
Parameter	Symbol	Value	Unit
Reverse Voltage	$V_{RM}$	250	V
Peak reverse voltage	$V_{RM}$	250	V
Continuous Forward Current	$I_o$	0.2	A
Non-repetitive Peak Forward Current @ $t=1\mu\text{s}$	$I_{FSM}$	2.5	A
Power Dissipation	$P_D$	0.2	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$
Thermal Resistance	$R_{JA}$	625	$^\circ\text{C}/\text{W}$

### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	$V_{BR}$	$I_R = 100\mu\text{A}$	250			V
Forward voltage	$V_F$	$I_F = 100\text{mA}$			1	V
		$I_F = 200\text{mA}$			1.25	V
Reverse current	$I_R$	$V_R = 200\text{V}$			100	nA
		$V_R = 200\text{V}, T_a = 150^\circ\text{C}$			100	$\mu\text{A}$
Typical Junction Capacitance	$C_J$	$V_R = 0\text{V}, f = 1.0\text{MHz}$			5	pF
Reverse Recovery Time	$T_{RR}$	$I_F = 30\text{mA}, I_R = 3\text{mA}, I_{RR} = 3\text{mA}, R_L = 100 \Omega$			50	ns

## Typical Characteristics



**SOT-323 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.800	1.100	0.031	0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	1.100	0.031	0.043
b	0.200	0.400	0.008	0.016
c	0.050	0.150	0.002	0.006
D	1.900	2.200	0.075	0.087
E	2.000	2.450	0.079	0.096
E1	1.150	1.350	0.045	0.053
e	0.650TYP.		0.026TYP.	
e1	1.200	1.400	0.047	0.055
L	0.200	0.460	0.008	0.018
θ	0°	8°	0°	8°